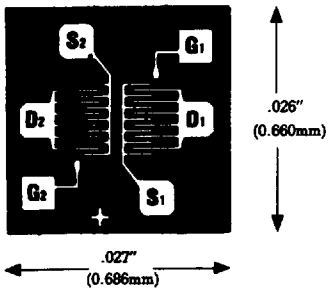
N-CHANNEL DUAL JUNCTION FET

CHIP NUMBER

DMN36.1A



Die Size: .26 x 27 (mils)
0.660 x 0.686(mm)
3.5 x 3.5(mils)
Pad Size: 0.089 x 0.089(mm)

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the die be eutectically mounted with gold silicon preform 98/2%.

b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

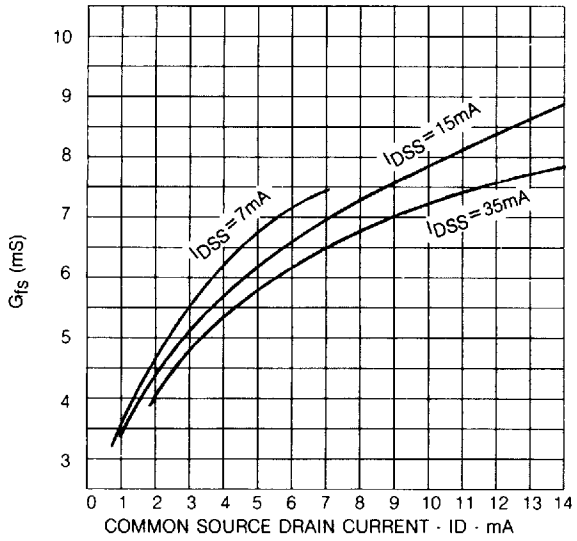
PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV_{GSS}	-25	-35		V	V_{DS} = 0, I_G = 1μA
I_{DSS}	5	20	40	mA	V_{DS} = 10V, V_{GS} = 0
V_p	-1		-6	V	V_{DS} = 10V, I_D, = 1nA
I_{GSS}		10	100	pA	V_{DS} = 0, V_{GS} = -15V
g_{fs}	4.5	6.0	10	ms	V_{DS} = 10V, I_D = 5mA, f = 1MHz
C_{rss}		1.0	1.5	pF	V_{DS} = 10V, I_D = 5mA, f = 1MHz
$\bar{e}_n$		4	20	nV/√Hz	V_{DS} = 10V, I_D = 5mA, f = 1KHz

TYPICAL DEVICE TYPES: 2N5911, 2N5912, U257

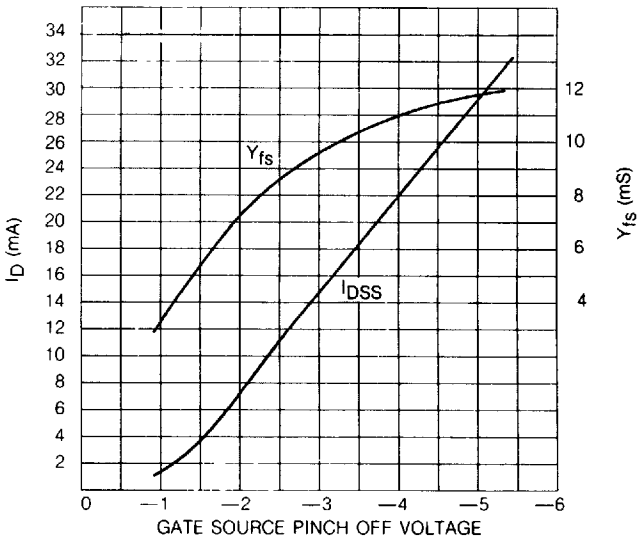
N-CHANNEL DUAL JUNCTION FET

CHIP TYPE DMN3611A

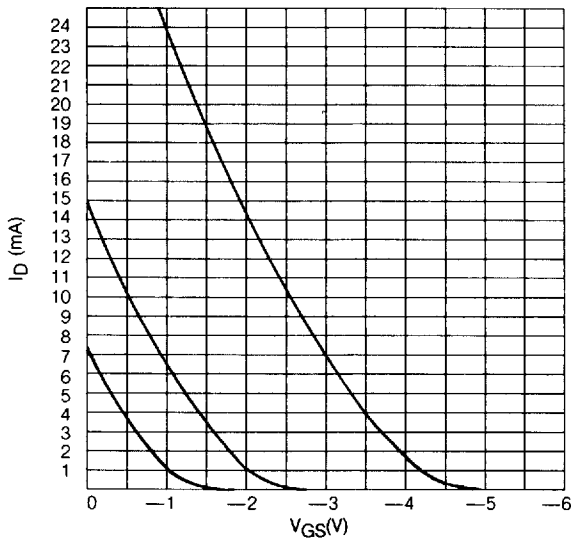
COMMON SOURCE, SHORT CIRCUIT FORWARD TRANSADMITTANCE VS OPERATING DRAIN CURRENT



ZERO GATE VOLTAGE DRAIN CURRENT · IDSS mA



TRANSFER CHARACTERISTIC



COMMON SOURCE DRAIN CHARACTERISTICS